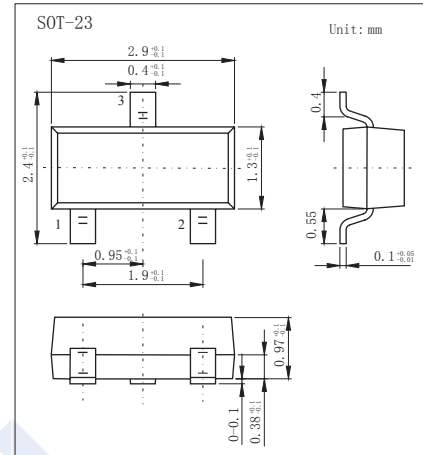
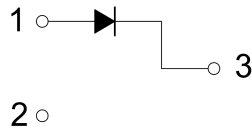


Schottky Diodes

RB411D (KB411D)

■ Features

- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Peak Reverse Voltage	V_{RM}	40	V
RMS reverse voltage	$V_{R(RMS)}$	28	
DC Blocking Voltage	V_R	20	
Average Rectified Output Current	I_o	0.5	A
Peak Forward Surge Current	I_{FM}	3	
Power Dissipation	P_D	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	500	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	$I_R = 100 \mu\text{A}$	40			V
Forward voltage	V_F	$I_F = 10\text{mA}$			0.3	
		$I_F = 500\text{mA}$			0.5	
Reverse voltage leakage current	I_R	$V_R = 10\text{V}$			30	μA
Capacitance between terminals	C_T	$V_R = 10\text{V}, f = 1\text{MHz}$		20		pF

■ Marking

Marking	D3E
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Schottky Diodes

RB411D (KB411D)

■ Typical Characteristics

